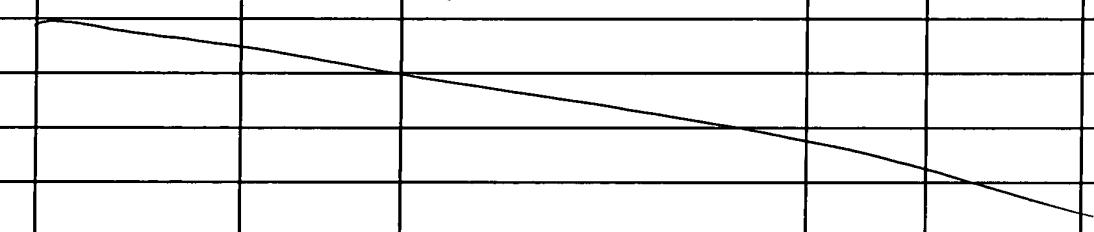
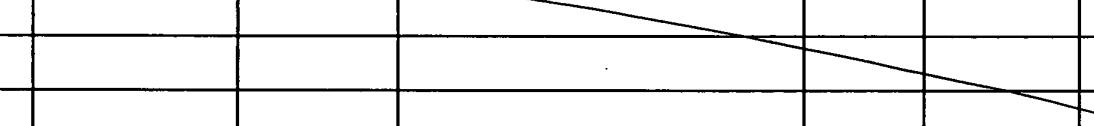
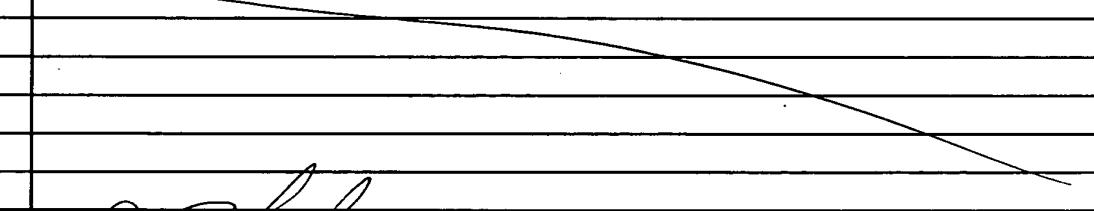


<b>INFORMATION DISCLOSURE CITATION</b>  PTO-1449			ATTORNEY'S DKT NO. 025219-382		APPLICATION NO. Unassigned	
			APPLICANT Bernard Aspar, et al.			
			FILING DATE Herewith		GROUP Unassigned	
<b>U.S. PATENT DOCUMENTS</b>						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
NPW	5,256,581	10/26/93	Foerstner, et. al.	437	24	
NPW	5,374,564	12/20/94	Bruel	437	24	
NPW	5,783,477	07/21/98	Kish, Jr. et. al.	438	455	
NPW	5,953,622	09/14/99	Lee, et al.	438	458	
NPW	5,993,677	11/30/99	Biasse, et al.	216	36	11046 U.S. PTO 10/07/99
NPW	6,013,563	01/11/00	Henley, et al.	438	458	02/06/02
NPW	6,020,252	02/01/00	Aspar, et al.	438	458	
						
<b>FOREIGN PATENT DOCUMENTS</b>						
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation
						Yes
NPW	2 758 907	07/31/98	France			
						
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
NPW	Hiroshi Wada, et al.: "Electrical Characteristics Of Directly-Bonded GaAs and InP" Applied Physics Letters, vol. 62, no. 7, 15 February 1993, pages 738-740, XP000338292					
						
EXAMINER 	DATE CONSIDERED 1/21/03					

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.